RT3AMMAM1-T150

Composite Transistor For Low Frequency Amplify Application Silicon PNP Epitaxial Type

AEC-Q101 Compliance

DESCRIPTION

RT3AMMAM1 is compound transistor built with two $ISA1235A\,chips$ in SC-88 package.

FEATURE

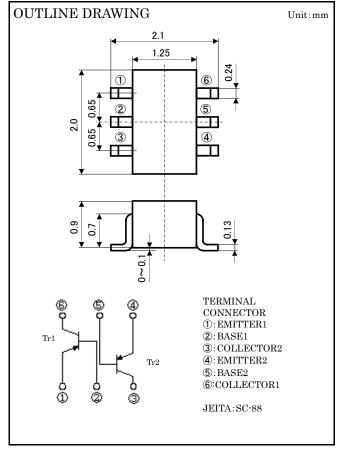
Silicon PNP epitaxial type

Each transistor elements are independent.

Mini package for easy mounting.

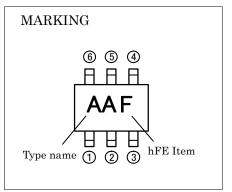
APPLICATION

For low frequency amplify application.



MAXIMUM RATING (Ta=25°C)(Tr1,Tr2)

| SYMBOL | PARAMETER | RATING | UNIT | |
|------------------|------------------------------|----------|------|--|
| Vcbo | Collector to Base voltage | -60 | V | |
| VEBO | Emitter to Base voltage | -6 | V | |
| VCEO | Collector to Emitter voltage | -50 | V | |
| I_{C} | Collector current | -200 | mA | |
| PT | Total dissipation | 200 | mW | |
| Tj | Junction temperature | +150 | ပ္ | |
| $T_{ m stg}$ | Storage temperature | -55~+150 | လူ | |



ELECTRICAL CHARACTERISTICS (Ta=25°C)(Tr1,Tr2)

| Symbol | Parameter | Test conditions | Limits | | | Unit |
|-----------------------|---|---|--------|-----|------|------|
| | | lest conditions | Min | Typ | Max | Unit |
| V(BR)CEO | Collector to Emitter breakdown voltage | I _C =100 μ A,R _{BE} =∞ | -50 | ı | _ | V |
| Ісво | Collector cut off current | V _{CB} =-60V,I _E =0 | _ | 1 | -0.1 | μΑ |
| IEBO | Emitter cut off current | V_{EB} =-6 V , I_{C} =0 | _ | - | -0.1 | μΑ |
| hfe* | DC forward current gain | VCE=-6V,IC=-1mA | 150 | ı | 500 | _ |
| hfe | DC forward current gain | Vce=-6V,Ic=-0.1mA | 90 | 1 | _ | _ |
| V _{CE} (sat) | Collector to Emitter saturation voltage | I _C =-100mA,I _B =-10mA | _ | - | -0.3 | V |
| f_{T} | Gain band width product | V _{CE} =-6V,I _E =10mA | _ | 200 | _ | MHz |
| C_{ob} | Collector output capacitance | V _{CB} =-6V,I _E =0,f=1MH _Z | _ | 4.0 | _ | pF |
| NF | Noise figure | V_{CE} =6 V_{IE} =0.3 mA_{f} =100 Hz_{RG} =10 $k\Omega$ | _ | 1 | 20 | dB |

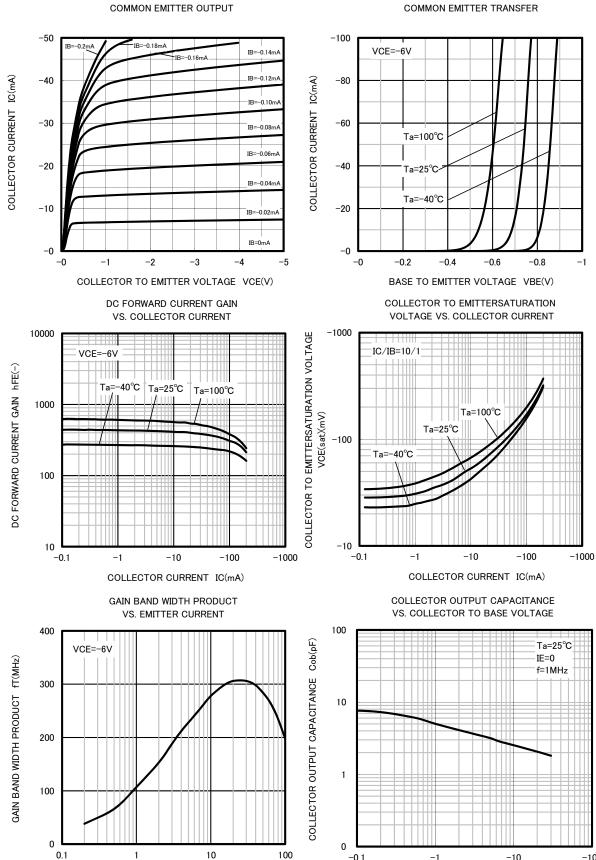
^{*:} It shows hee classification in right table.

| item | E | F |
|-------------|---------|---------|
| $_{ m hFE}$ | 150~300 | 250~500 |

RT3AMMAM1-T150

Composite Transistor For Low Frequency Amplify Application Silicon PNP Epitaxial Type

TYPICAL CHARACTERISTICS (Tr1,Tr2.)



EMITTER CURRENT IE(mA)

-0.1

-10

COLLECTOR TO BASE VOLTAGE VCB(V)

-100



Keep safety first in your circuit designs!

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